

INCHANGE Semiconductor

isc Product Specification

isc Silicon NPN Darlington Power Transistor

BU826A

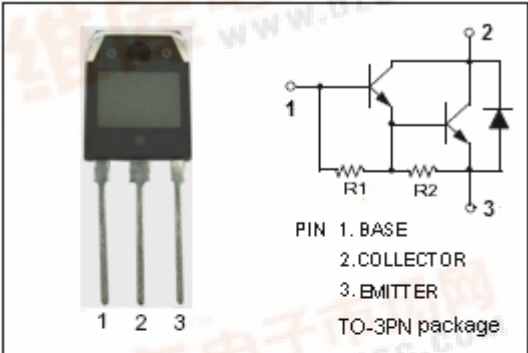
DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)}=400V(\text{Min})$
- High Switching Speed

APPLICATIONS

Designed for line operated switchmode applications such as:

- Switching regulators
- Inverters
- Solenoid and relay drivers

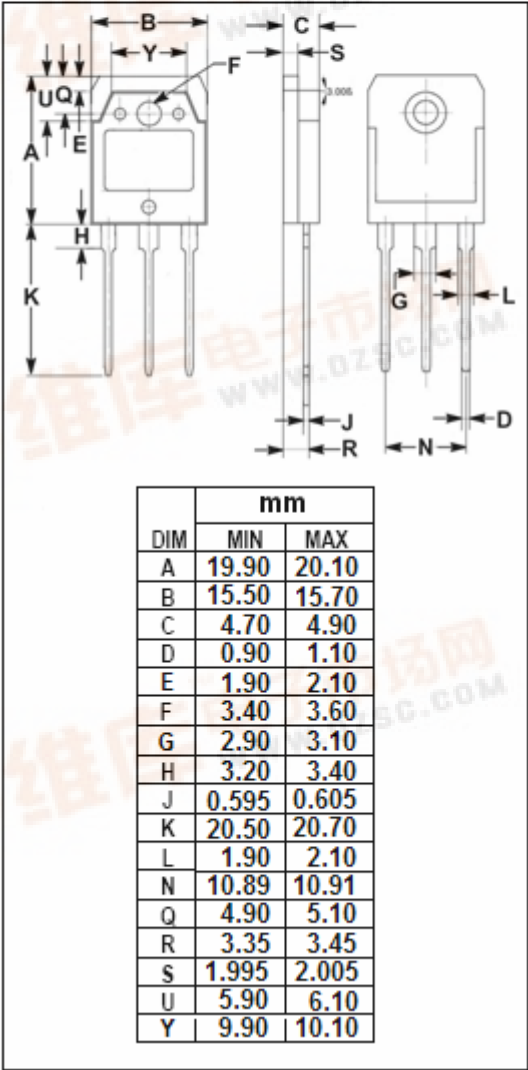


ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage($V_{BE}=0$)	1000	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current-Continuous	6	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current	0.5	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	125	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^{\circ}\text{C/W}$



isc Silicon NPN Darlington Power Transistor**BU826A****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}$; $I_B=0$, $L=25\text{mH}$	400			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=2.5\text{A}$; $I_B=55\text{mA}$			2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}$; $I_B=0.2\text{A}$			2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2.5\text{A}$; $I_B=55\text{mA}$			2.2	V
I_{CES}	Collector Cutoff Current	$V_{CE}=\text{Rated } V_{CES}$; $R_{BE}=0$ $V_{CE}=\text{Rated } V_{CES}$; $R_{BE}=0$, $T_C=125^{\circ}\text{C}$			1.0 2.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=8\text{V}$; $I_C=0$			150	mA